

CMOS Low Power Dual 2:1 Mux/Demux USB 2.0 (480 Mbps)/USB 1.1 (12 Mbps)

ADG772

FEATURES

USB 2.0 (480 Mbps) and USB 1.1 (12 Mbps) signal switching compliant Tiny 10-lead 1.6 mm × 1.3 mm mini LFCSP package and 12-lead 3 mm × 3 mm LFCSP package 2.7 V to 3.6 V single-supply operation Typical power consumption: <0.1 μW RoHS compliant

APPLICATIONS

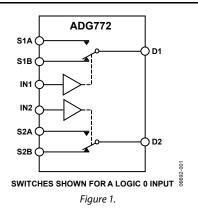
USB 2.0 signal switching circuits Cellular phones PDAs MP3 players Battery-powered systems Headphone switching Audio and video signal routing Communications systems

GENERAL DESCRIPTION

The ADG772 is a low voltage, CMOS device that contains two independently selectable single-pole, double throw (SPDT) switches. It is designed as a general-purpose switch and can be used for routing both USB 1.1 and USB 2.0 signals.

This device offers a data rate of 1260 Mbps, making the part suitable for high frequency data switching. Each switch conducts equally well in both directions when on and has an input signal range that extends to the supplies. The ADG772 exhibits break-before-make switching action.

The ADG772 comes in a 12-lead LFCSP, and a 10-lead mini LFCSP. These packages make the ADG772 the ideal solution for space-constrained applications.



PRODUCT HIGHLIGHTS

- 1. $1.6 \text{ mm} \times 1.3 \text{ mm}$ mini LFCSP package.
- 2. USB 1.1 (12 Mbps) and USB 2.0 (480 Mbps) compliant.
- 3. Single 2.7 V to 3.6 V operation.
- 4. RoHS compliant.

Rev. 0

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REVISION HISTORY

8/07—Revision 0: Initial Version

SPECIFICATIONS

 V_{DD} = 2.7 V to 3.6 V, GND = 0 V, unless otherwise noted.

Table 1.

Parameter	+25°C	-40°C to +85°C	Unit	Test Conditions/Comments
ANALOG SWITCH				
Analog Signal Range		0 V to V _{DD}	V	
On Resistance (R _{ON})	6.7		Ωtyp	$V_{DD} = 2.7 V$, $V_S = 0 V$ to V_{DD} , $I_S = 10 mA$; see Figure 21
		8.8	Ωmax	
On Resistance Match	0.04		Ωtyp	$V_{DD} = 2.7 \text{ V}, \text{ V}_{\text{S}} = 1.5 \text{ V}, \text{ I}_{\text{S}} = 10 \text{ mA}$
Between Channels (ΔR _{ON})		0.2	Ωmax	
On Resistance Flatness (R _{FLAT (ON)})	3.3		Ωtyp	$V_{DD} = 2.7 \text{ V}, \text{ V}_{\text{S}} = 0 \text{ V} \text{ to } \text{ V}_{\text{DD}}, \text{ I}_{\text{S}} = 10 \text{ mA}$
		3.6	Ωmax	
LEAKAGE CURRENTS				$V_{DD} = 3.6 V$
Source Off Leakage Is (Off)	±0.2		nA typ	$V_{\rm S} = 0.6 \text{V}/3.3 \text{V}, V_{\rm D} = 3.3 \text{V}/0.6 \text{V}; \text{ see Figure 22}$
Channel On Leakage I _D , I _s (On)	±0.2		nA typ	$V_{s} = V_{D} = 0.6 V \text{ or } 3.3 V; \text{ see Figure } 23$
DIGITAL INPUTS				
Input High Voltage, V _{INH}		2	V min	
Input Low Voltage, VINL		0.8	V max	
Input Current				
Inl or Inh	0.005		μA typ	$V_{IN} = V_{INL} \text{ or } V_{INH}$
		±0.1	μA max	$V_{IN} = V_{INL} \text{ or } V_{INH}$
C _{IN} , Digital Input Capacitance	2		pF typ	
DYNAMIC CHARACTERISTICS ¹				
t _{on}	9		ns typ	$R_L = 50 \Omega$, $C_L = 35 pF$
	12.5	13.5	ns max	$V_s = 2 V$; see Figure 24
t _{OFF}	6		ns typ	$R_L = 50 \Omega$, $C_L = 35 pF$
	9.5	10	ns max	$V_s = 2 V$; see Figure 24
Propagation Delay	250		ps typ	$R_L = 50 \Omega$, $C_L = 35 pF$
Propagation Delay Skew, tskew	20		ps typ	$R_L = 50 \Omega$, $C_L = 35 pF$
Break-Before-Make Time Delay (t _{BBM})	5		ns typ	$R_L = 50 \Omega$, $C_L = 35 pF$
	3.4	2.9	ns min	$V_{S1} = V_{S2} = 2 V$; see Figure 25
Charge Injection	0.5		pC typ	$V_D = 1.25 V$, $R_s = 0 \Omega$, $C_L = 1 nF$; see Figure 26
Off Isolation	73		dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$; see Figure 27
Channel-to-Channel Crosstalk	-90		dB typ	S1A to S2A/S1B to S2B; $R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$; see Figure 28
	-80		dB typ	S1A to S1B/S2A to S2B; $R_L = 50 \Omega$, $C_L = 5 pF$, f = 1 MHz; see Figure 29
–3 dB Bandwidth	630		MHz typ	$R_L = 50 \Omega$, $C_L = 5 pF$; see Figure 30
Data Rate	1260		Mbps typ	$R_L = 50 \Omega$, $C_L = 5 pF$; see Figure 30
C _s (Off)	2.4		pF typ	
C _D , C _s (On)	6.9		pF typ	
POWER REQUIREMENTS				V _{DD} = 3.6 V
IDD	0.006		μA typ	Digital inputs = 0 V or 3.6 V
		1	µA max	

¹ Guaranteed by design, not subject to production test.

ABSOLUTE MAXIMUM RATINGS

 $T_A = 25^{\circ}C$, unless otherwise noted.

Table 2.

Parameter	Rating	
V _{DD} to GND	–0.3 V to +4.6 V	
Analog Inputs ¹ , Digital Inputs	-0.3 V to V _{DD} + 0.3 V or 10 mA, whichever occurs first	
Peak Current, Pin S1A, Pin S2A, Pin D1, or Pin D2	100 mA (pulsed at 1 ms, 10% duty cycle max)	
Continuous Current, Pin S1A, Pin S2A, Pin D1, or Pin D2	30 mA	
Operating Temperature Industrial		
Range (B version)	–40°C to +85°C	
Storage Temperature Range	–65°C to +150°C	
Junction Temperature	150°C	
10-Lead Mini LFCSP (4-Layer Board)		
θ_{JA} Thermal Impedance	131.6°C/W	
12-Lead LFCSP (4-Layer Board)		
θ_{JA} Thermal Impedance	61°C/W	
Pb-Free Temperature, Soldering,		
IR Reflow		
Peak Temperature	260(+0/-5)°C	
Time at Peak Temperature	10 sec to 40 sec	

¹ Overvoltages at the IN1, IN2, S1A, S2A, D1, or D2 pins are clamped by internal diodes. Current should be limited to the maximum ratings given.

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Only one absolute maximum rating may be applied at any one time.

ESD CAUTION



ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

PIN CONFIGURATION AND FUNCTION DESCRIPTIONS

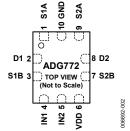
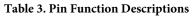
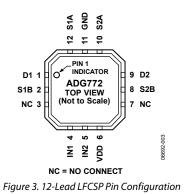


Figure 2. 10-Lead Mini LFCSP Pin Configuration





10-Lead Mini LFCSP	12-Lead LFCSP	Mnemonic	Description	
1	12	S1A	A Source Terminal. Can be an input or an output.	
2	1	D1	Drain Terminal. Can be an input or an output.	
3	2	S1B	Source Terminal. Can be an input or an output.	
4	4	IN1	Logic Control Input. Controls Switch S1A/S1B—D1.	
5	5	IN2	Login Control Input. Controls Switch S2A/S2B—D2.	
6	6	VDD	Most Positive Power Supply Potential.	
7	8	S2B	Source Terminal. Can be an input or an output.	
8	9	D2	Drain Terminal. Can be an input or an output.	
9	10	S2A	Source Terminal. Can be an input or an output.	
10	11	GND	Ground (0 V) Reference.	
N/A	3, 7	NC	No Connect.	

TRUTH TABLE

Table 4.

Logic (IN1/IN2)	Switch A (S1A or S2A)	Switch B (S1B or S2B)
0	Off	On
1	On	Off

TYPICAL PERFORMANCE CHARACTERISTICS

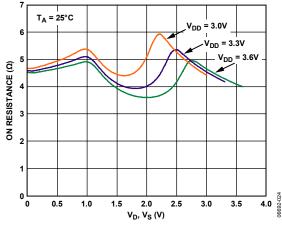


Figure 4. On Resistance vs. V_D (V_S) $V_{DD} = 3.0$ V to 3.6 V

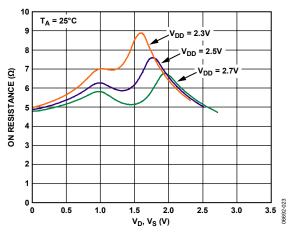


Figure 5. On Resistance vs. V_D (V_s) V_{DD} = 2.5 V ± 0.2 V

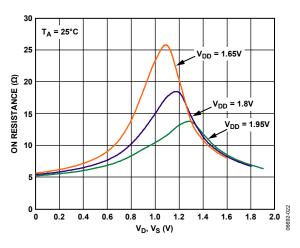


Figure 6. On Resistance vs. V_D (V_s) V_{DD} = 1.8 V ± 0.15 V

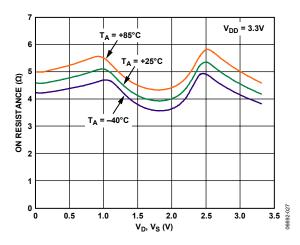


Figure 7. On Resistance vs. V_D (V_s) for Different Temperature, V_{DD} = 3.3 V

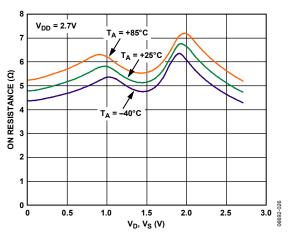


Figure 8. On Resistance vs. V_D (V_s) for Different Temperature, $V_{DD} = 2.7 V$

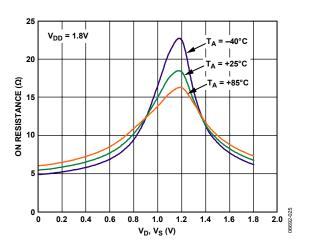


Figure 9. On Resistance vs. V_D (V_s) for Different Temperatures, $V_{DD} = 1.8$ V

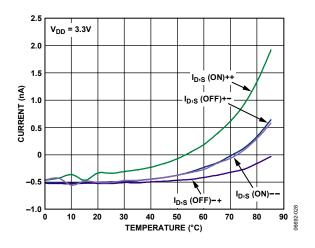


Figure 10. Leakage Current vs. Temperature, V_{DD} = 3.3 V

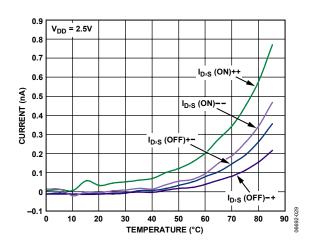


Figure 11. Leakage Current vs. Temperature, $V_{DD} = 2.5 V$

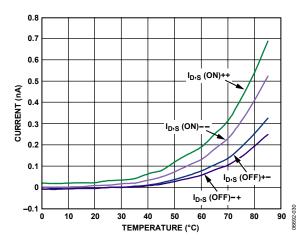


Figure 12. Leakage Current vs. Temperature, $V_{DD} = 1.8 V$

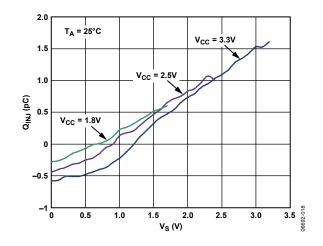


Figure 13. Charge Injection vs. Source Voltage

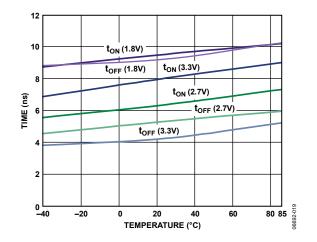


Figure 14. ton/toff Times vs. Temperature

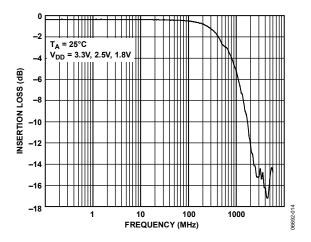


Figure 15. Bandwidth

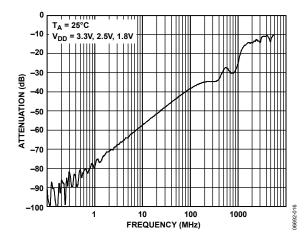
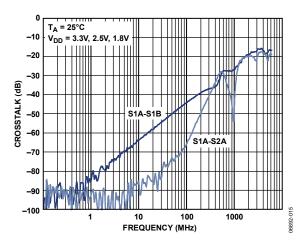


Figure 16. Off Isolation vs. Frequency





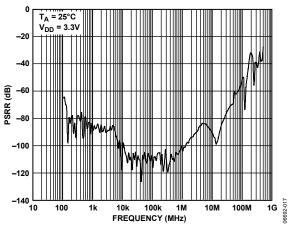


Figure 18. PSRR vs. Frequency

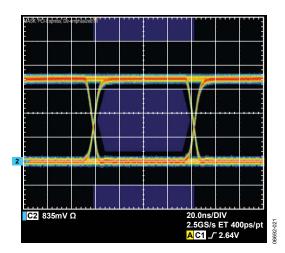


Figure 19. USB 1.1 Eye Diagram

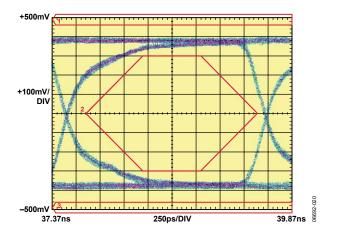
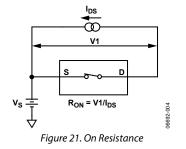
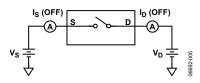


Figure 20. USB 2.0 Eye Diagram

TEST CIRCUITS





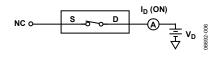


Figure 22. Off Leakage

Figure 23. On Leakage

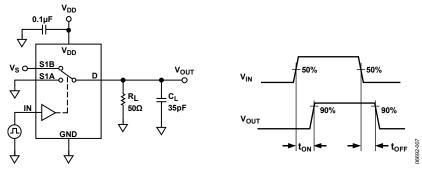
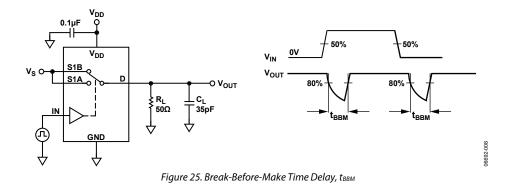


Figure 24. Switching Times, ton, toff



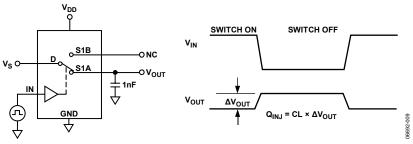


Figure 26. Charge Injection

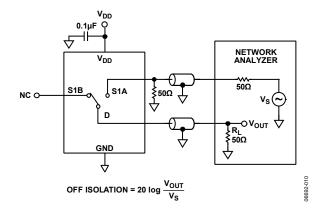


Figure 27. Off Isolation

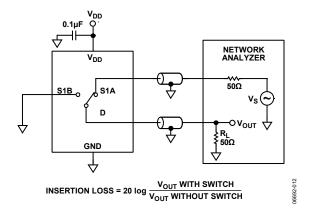
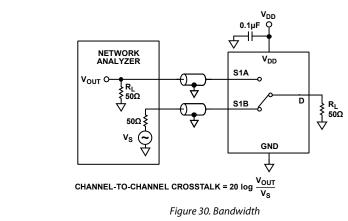


Figure 29. Channel-to-Channel Crosstalk (S1A–S1B)

06692-011



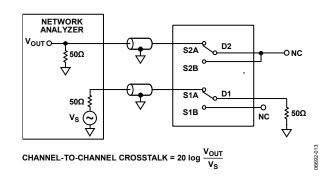


Figure 28. Channel-to-Channel Crosstalk (S1A-S2A)

TERMINOLOGY

Idd

Positive supply current.

 $\mathbf{V}_{\mathrm{D}}\left(\mathbf{V}s\right)$ Analog voltage on Terminal D and Terminal S.

R_{ON} Ohmic resistance between Terminal D and Terminal S.

R_{FLAT} (On) The difference between the maximum and minimum values of on resistance as measured on the switch.

 ΔR_{ON} On resistance match between any two channels.

Is (Off) Source leakage current with the switch off.

I_D (Off) Drain leakage current with the switch off.

I_D, I_s (On) Channel leakage current with the switch on.

V_{INL} Maximum input voltage for Logic 0.

 $V_{\mbox{\scriptsize INH}}$ Minimum input voltage for Logic 1.

I_{INL} (I_{INH}) Input current of the digital input.

C_s (Off) Off switch source capacitance. Measured with reference to ground.

 C_D (Off) Off switch drain capacitance. Measured with reference to ground.

C_D, C_s (On) On switch capacitance. Measured with reference to ground. C_{IN}

Digital input capacitance.

ton

Delay time between the 50% and 90% points of the digital input and switch on condition.

t_{OFF} Delay time between the 50% and 90% points of the digital input and switch off condition.

 t_{BBM} On or off time measured between the 80% points of both switches when switching from one to another.

Charge Injection Measure of the glitch impulse transferred from the digital input to the analog output during on/off switching.

Off Isolation Measure of unwanted signal coupling through an off switch.

Crosstalk Measure of unwanted signal that is coupled from one channel to another as a result of parasitic capacitance.

-3 dB Bandwidth Frequency at which the output is attenuated by 3 dB.

On Response Frequency response of the on switch.

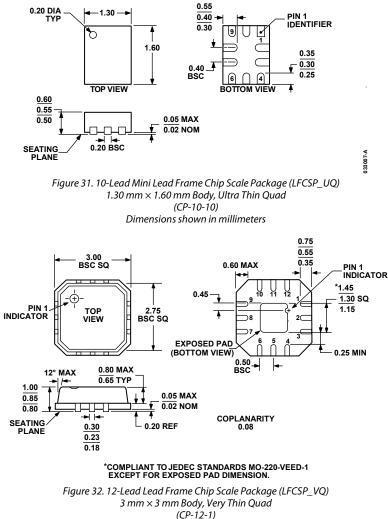
Insertion Loss The loss due to the on resistance of the switch.

THD + N Ratio of the harmonics amplitude plus noise of a signal to the fundamental.

Tskew

The measure of the variation in propagation delay between each channel.

OUTLINE DIMENSIONS



Dimensions shown in millimeters

ORDERING GUIDE

Model	Temperature Range	Package Description	Package Option	Branding
ADG772BCPZ-1REEL ¹	-40°C to +85°C	12-Lead Lead Frame Chip Scale Package (LFCSP_VQ)	CP-12-1	S2P
ADG772BCPZ-REEL ¹	–40°C to +85°C	10-Lead Mini Lead Frame Chip Scale Package (LFCSP_UQ)	CP-10-10	В
ADG772BCPZ-REEL71	–40°C to +85°C	10-Lead Mini Lead Frame Chip Scale Package (LFCSP_UQ)	CP-10-10	В
EVAL-ADG772EBZ ¹	-40°C to +85°C	Evaluation Board		

 1 Z = RoHS Compliant Part.



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